

# Silicon Carbide Schottky Diode

650 V, 4 A

## FFSB0465A

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 25 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb-Free, Halogen Free/BFR Free and RoHS Compliant

### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

### ABSOLUTE MAXIMUM RATINGS

(T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSB0465A	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		25	mJ
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 160°C		4	A
	Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C		7.7	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	360	A
		T <sub>C</sub> = 150°C, 10 μs	330	
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	38	A
I <sub>F, RM</sub>	Repetitive Forward Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	18	A
P <sub>tot</sub>	Power Dissipation	T <sub>C</sub> = 25°C	63	W
		T <sub>C</sub> = 150°C	10.5	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

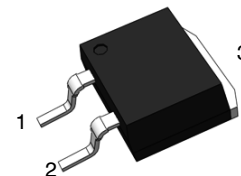
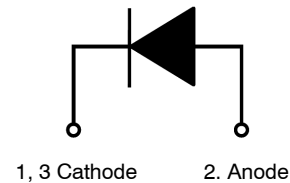
1. E<sub>AS</sub> of 25 mJ is based on starting T<sub>J</sub> = 25°C, L = 0.5 mH, I<sub>AS</sub> = 10 A, V = 50 V.



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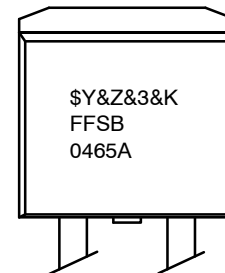
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### ELECTRICAL CONNECTION



D<sup>2</sup>PAK2 (TO-263-2L)  
CASE 418BK

### MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FFSB0465A	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# FFSB0465A

## THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.38	$^{\circ}\text{C}/\text{W}$

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method†	Reel Size	Tape Width	Quantity
FFSB0465A	FFSB0465A	D2PAK	Tape/Reel	N/A	N/A	800 Units

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## ELECTRICAL CHARACTERISTICS $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage	$I_F = 4\text{ A}, T_C = 25^{\circ}\text{C}$	–	1.50	1.75	V
		$I_F = 4\text{ A}, T_C = 125^{\circ}\text{C}$	–	1.6	2.0	
		$I_F = 4\text{ A}, T_C = 175^{\circ}\text{C}$	–	1.72	2.4	
$I_R$	Reverse Current	$V_R = 650\text{ V}, T_C = 25^{\circ}\text{C}$	–	–	200	$\mu\text{A}$
		$V_R = 650\text{ V}, T_C = 125^{\circ}\text{C}$	–	–	400	
		$V_R = 650\text{ V}, T_C = 175^{\circ}\text{C}$	–	–	600	
$Q_C$	Total Capacitive Charge	$V = 400\text{ V}$	–	16	–	nC
C	Total Capacitance	$V_R = 1\text{ V}, f = 100\text{ kHz}$	–	258	–	pF
		$V_R = 200\text{ V}, f = 100\text{ kHz}$	–	29	–	
		$V_R = 400\text{ V}, f = 100\text{ kHz}$	–	21	–	

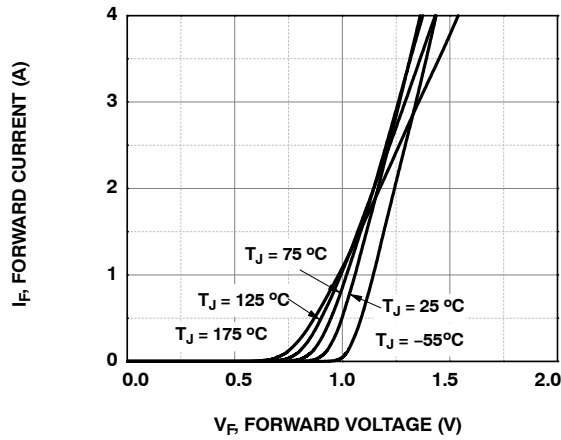
TYPICAL CHARACTERISTICS  $T_J = 25^\circ\text{C}$  Unless Otherwise Noted

Figure 1. Forward Characteristics

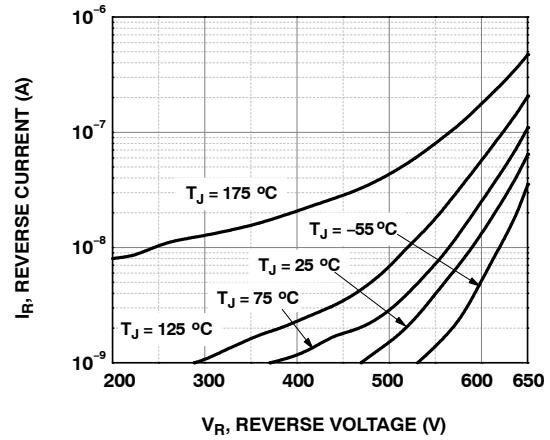


Figure 2. Reverse Characteristics

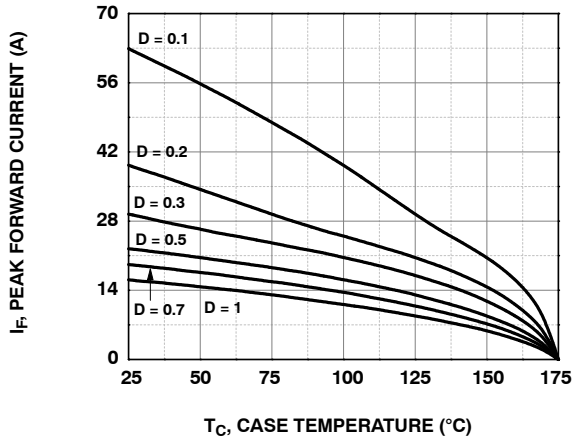


Figure 3. Current Derating

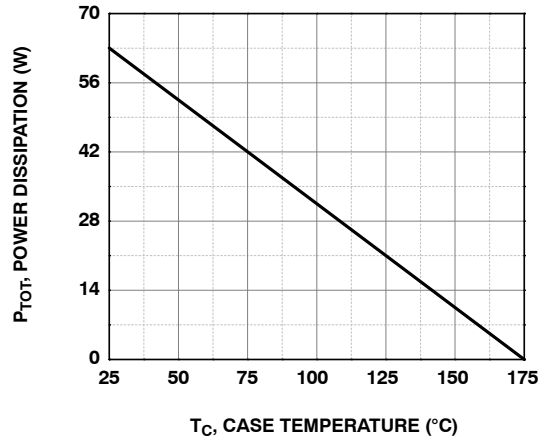


Figure 4. Power Derating

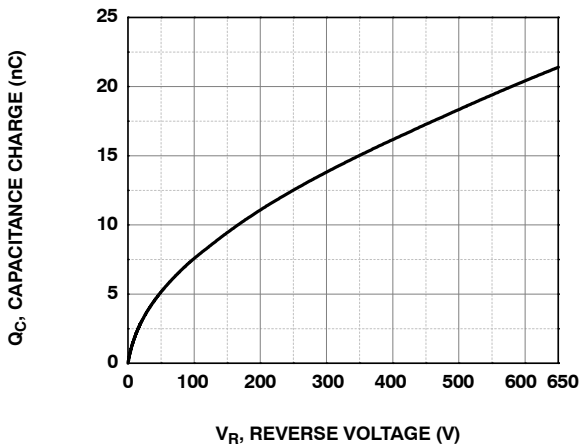


Figure 5. Capacitance Charge vs. Reverse Voltage

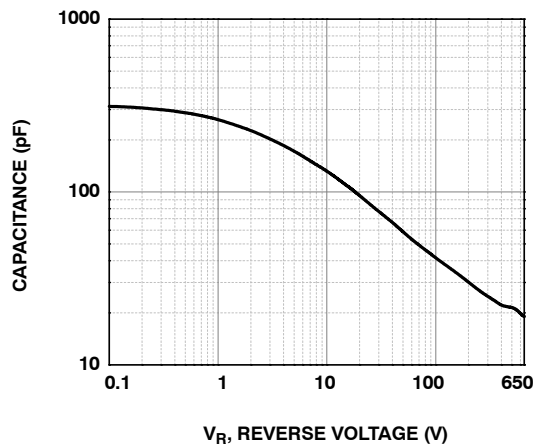


Figure 6. Capacitance vs. Reverse Voltage

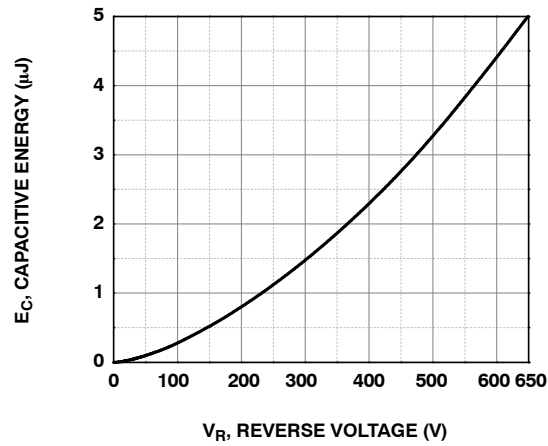
TYPICAL CHARACTERISTICS  $T_J = 25^\circ\text{C}$  Unless Otherwise Noted (continued)

Figure 7. Capacitance Stored Energy

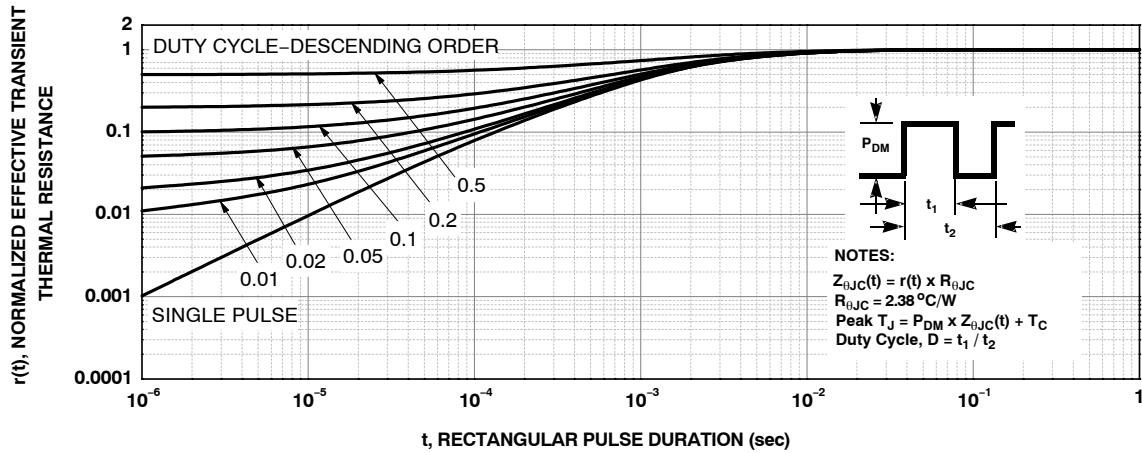


Figure 8. Junction-to-Case Transient Thermal Response Curve

## TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$   
 $R < 0.1 \Omega$   
 $V_{DD} = 50 \text{ V}$

$E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$   
 $Q1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)} \text{)}$

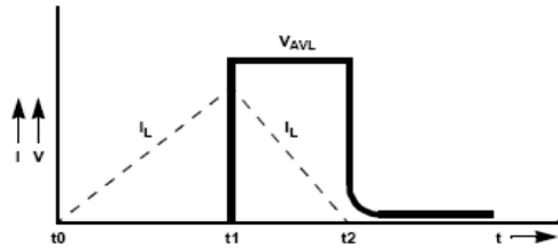
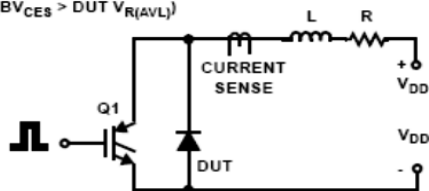
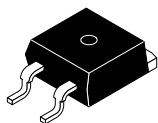


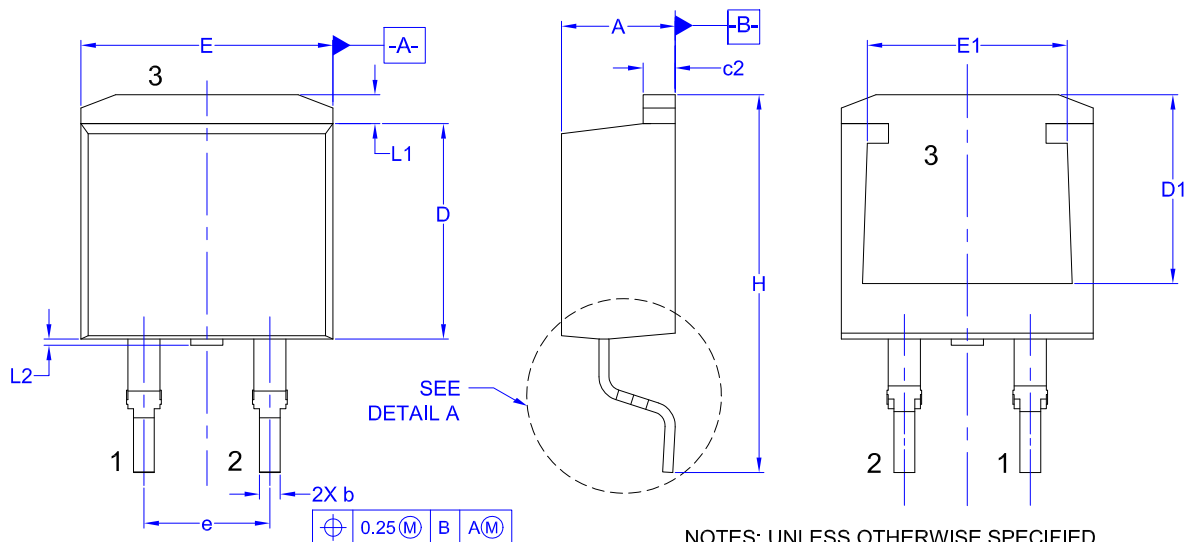
Figure 9. Unclamped Inductive Switching Test Circuit &amp; Waveform

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

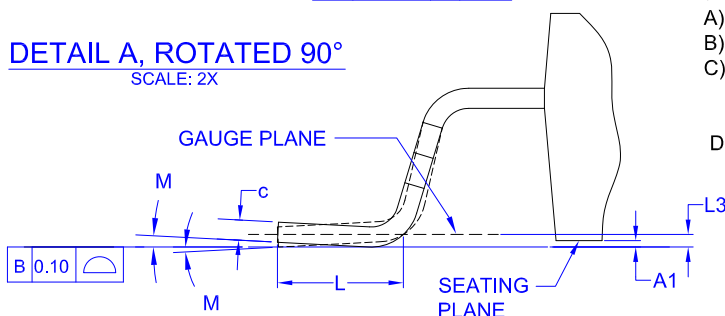


**D<sup>2</sup>PAK2 (TO-263-2L)**  
**CASE 418BK**  
**ISSUE O**

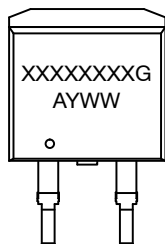
DATE 02 AUG 2018



**DETAIL A, ROTATED 90°**  
SCALE: 2X

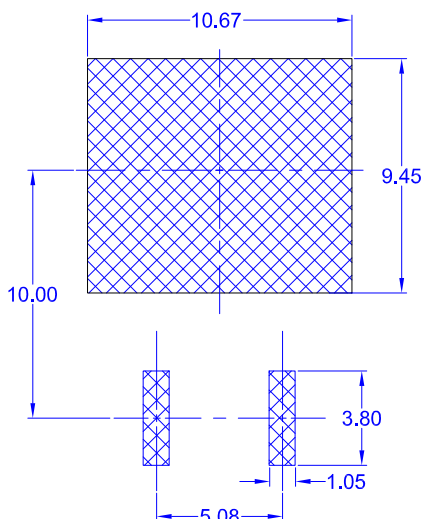


**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**LAND PATTERN RECOMMENDATION**  
**UNLESS NOTED, ALL DIMS TYPICAL**

NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) REFERENCE JEDEC, TO-263, VARIATION AB.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
- D) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.06	4.57	4.83
A1	0.00	0.10	0.25
b	0.51	0.81	0.99
c	0.30	0.407	0.74
c2	1.14	1.30	1.65
D	8.38	8.69	9.65
D1	7.30	7.80	8.30
E	9.65	10.16	10.67
E1	8.00	8.62	9.00
e	5.08 BSC		
H	14.60	15.35	15.88
L	1.78	2.54	2.79
L1	0.90	1.29	1.68
L2	0.00	0.15	0.25
L3	0.25 BSC		
M	0°	4°	8°

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